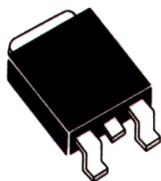




CJD340 NPN
CJD350 PNP

COMPLEMENTARY SILICON
POWER TRANSISTOR

DPAK **POWER!**™



DPAK CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD340, CJD350 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for high voltage general purpose applications.

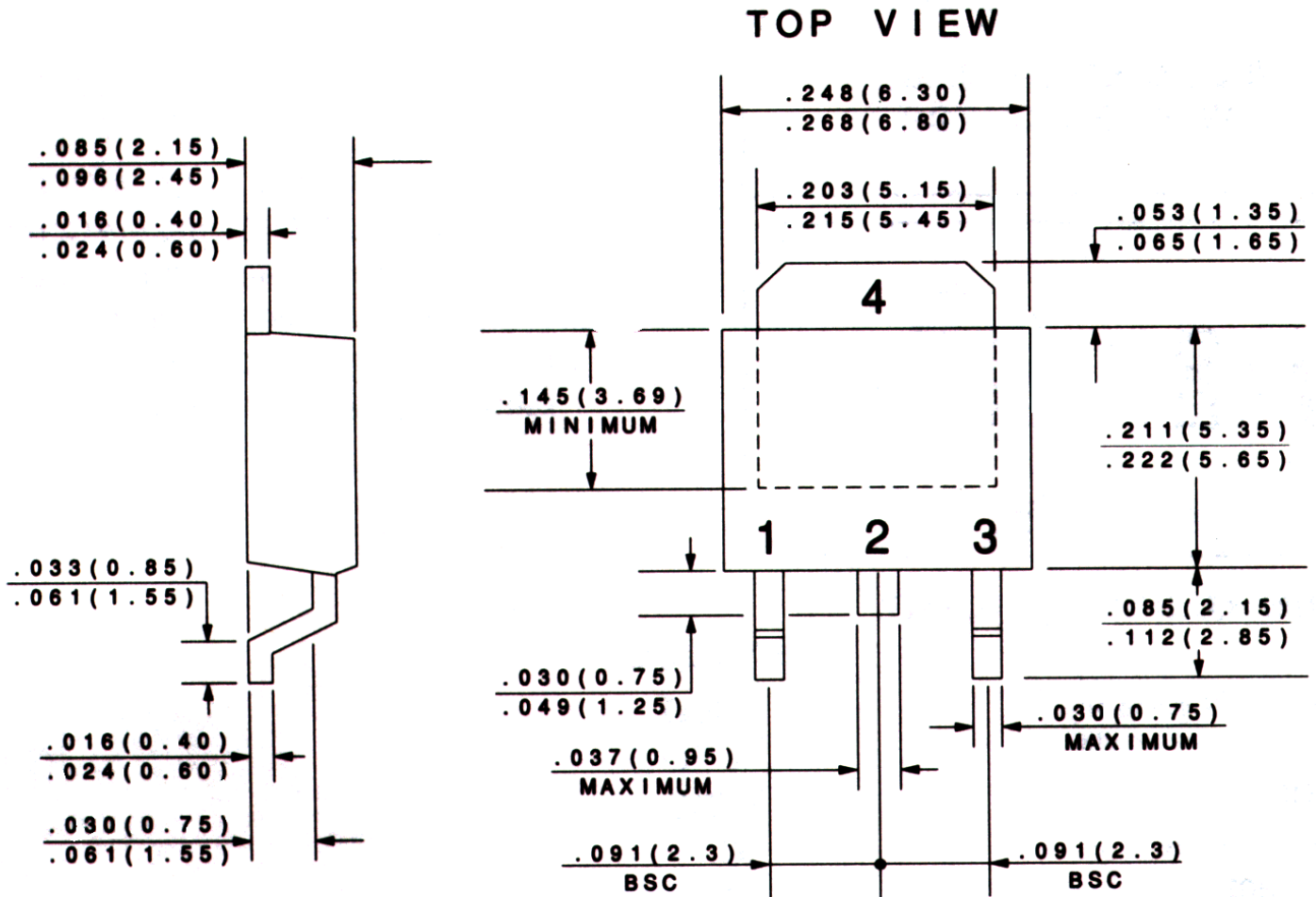
MAXIMUM RATINGS ($T_C=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Continuous Collector Current	I_C	500	mA
Peak Collector Current	I_{CM}	750	mA
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	15	W
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	1.56	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JC}	8.33	$^\circ\text{C/W}$
Thermal Resistance	θ_{JA}	80.1	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=300\text{V}$		100	μA
I_{EBO}	$V_{EB}=3.0\text{V}$		100	μA
BV_{CEO}	$I_C=1.0\text{mA}$	300		V
h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$	30	240	

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR